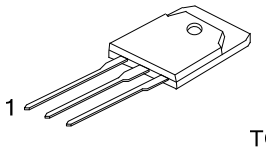
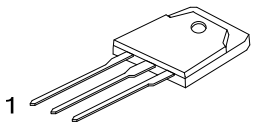
2SC4467

NPN EPITAXIAL SILICON TRANSISTOR

SILICON NPN TRIPLE DIFFUSED PLANAR TRANSISTOR



TO-3P



TO-3PN

■ DESCRIPTION

The UTC **2SC4467** is a silicon NPN triple diffused planar transistor, it uses UTC's advanced technology to provide the customers with high DC current gain and high collector-base breakdown voltage, etc.

The UTC **2SC4467** is suitable for audio and general purpose, etc.

■ FEATURES

* High DC current gain
* High collector-base breakdown voltage

■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
2SC4467L-x-T3P-T	2SC4467G-x-T3P-T	TO-3P	B	C	E	Tube
2SC4467L-x-T3N-T	2SC4467G-x-T3N-T	TO-3PN	B	C	E	Tube

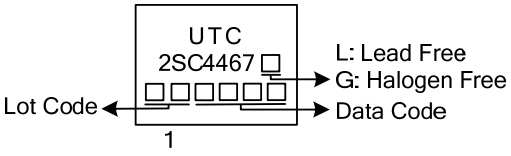
Note: Pin Assignment: B: Base C: Collector E: Emitter

2SC4467L-x-T3P-T

(1)Packing Type
(2)Package Type
(3)Rank
(4)Green Package

(1) T: Tube
(2) T3P: TO-3P, T3N: TO-3PN
(3) x: reference to Classification of h_{FE}
(4) L: Lead Free, G: Halogen Free and Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_A=25°C)

PARAMETER	SYMBOL	RATINGS	UNIT
Collector-Base Voltage	V_{CBO}	160	V
Collector-Emitter Voltage	V_{CEO}	120	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current	I_C	8	A
Base Current	I_B	3	A
Collector Power Dissipation (T_C=25°C)	P_C	80	W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

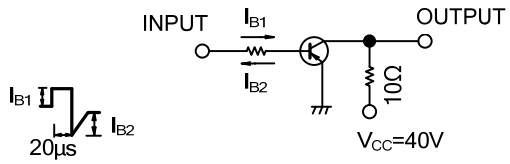
■ ELECTRICAL CHARACTERISTICS (T_A=25°C)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector Cut-Off Current		I_{CBO}	V_{CB}=160V			10	μA
Emitter Cut-Off Current		I_{EBO}	V_{EB}=6V			10	μA
Collector-Emitter Breakdown Voltage		BV_{CEO}	I_C=50mA	120			V
DC Current Gain		h_{FE}	V_{CE}=4V, I_C=3A	50			
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	I_C=3A, I_B=0.3A			1.5	V
Current Gain Bandwidth Product		f_T	V_{CE}=12V, I_E=-0.5A		20		MHz
Output Capacitance		C_{ob}	V_{CB}=10V, f=1MHz		200		pF
Switching time	Turn-on time	t_{ON}	V_{CC}=40V, R_L=10Ω, I_C=4A, I_{B1}=0.4A I_{B2}=0.4A		0.13		μS
	Storage time	t_S			3.50		μS
	Fall time	t_F			0.32		μS

■ CLASSIFICATION OF h_{FE}

RANK	O	P	Y
RANGE	50~100	70~140	90~180

■ TEST CIRCUIT



$I_{B1}=I_{B2}=0.4A$
DUTY CYCLE≤2%

■ TYPICAL CHARACTERISTICS